

Shottky Barrier Diode

FEATURES

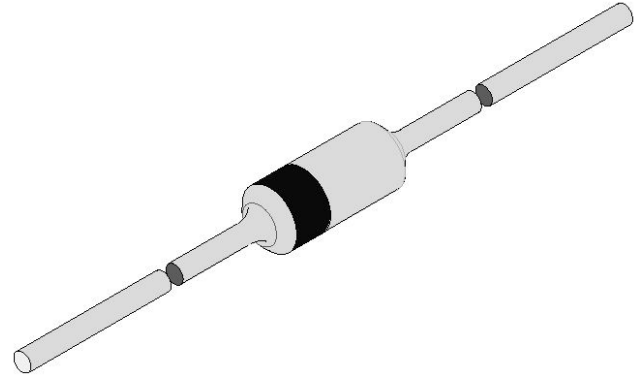
1. High reliability
2. Low reverse current and low forward voltage

APPLICATIONS

Low current certification and high speed switching.

CONSTRUCTION

Silicon epitaxial planar.



ABSOLUTE MAXIMUM RATINGS

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		1N60	V_{RRM}	40	V
		1N60P	V_{RRM}	45	V
Peak forward surge current	$t_p \leq 1\text{s}$	1N60	I_{FSM}	150	mA
		1N60P	I_{FSM}	500	mA
Forward continuous current	$T_a = 25^{\circ}\text{C}$	1N60	I_F	30	mA
		1N60P	I_F	50	mA
Storage temperature range			T_{stg}	-65~+125	$^{\circ}\text{C}$

MAXIMUM THERMAL RESISTANCE

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50mmx50mmx1.6mm	R_{thJA}	250	K/W

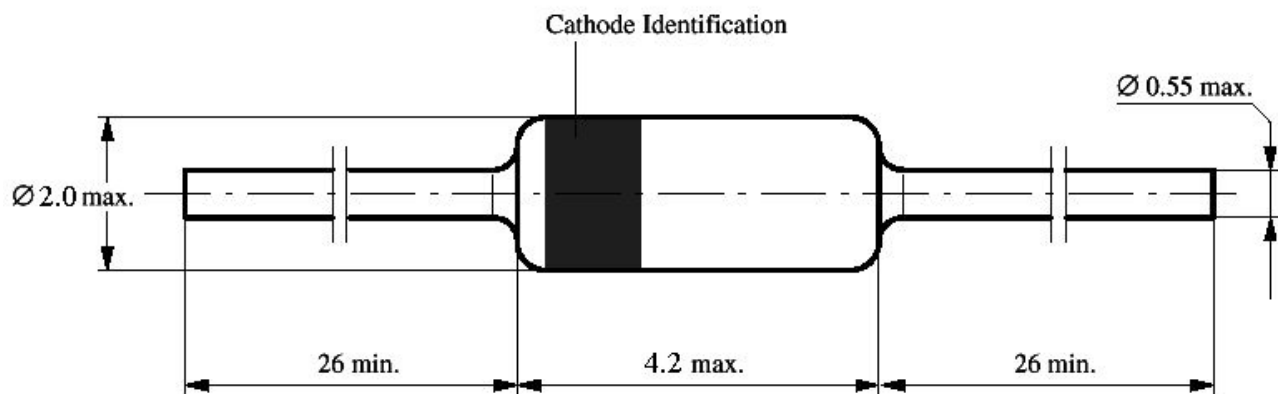
Shottky Barrier Diode

ABSOLUTE MAXIMUM RATINGS

T=25°C

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage	$I_F = 1\text{mA}$	1N60	V_F		0.32	0.5	V
		1N60P	V_F		0.24	0.5	V
	$I_F = 30\text{mA}$	1N60	V_F		0.65	1.0	V
		1N60P	V_F		0.65	1.0	V
Peak forward surge current	$V_R = 15\text{V}$	1N60	I_R		0.1	0.5	A
		1N60P	I_R		0.5	1.0	A
Forward continuous current	$V_R = 1\text{V}, f = 1\text{MHz}$	1N60	C_J		2.0		pF
	$V_R = 10\text{V}, f = 1\text{MHz}$	1N60P	C_J		6.0		pF
Storage temperature range	$I_F=1\text{mA}, I_T=1\text{mA}, R_c=100$		t_{rr}			1.0	ns

DIMENSION IN mm



Standard Glass Case
JEDEC DO 35